

<b>Form 1449 (Modified)</b>  <b>Information Disclosure Statement By Applicant</b>  (Use Several Sheets if Necessary)	<b>Atty Docket No.</b>	NOVLP091/NVLS-2889
	<b>Application No.:</b>	10/820,525
	<b>Applicants</b>	WU, Qingguo, et al.
	<b>Filing Date</b>	April 7, 2004
	<b>Group</b>	2823
	<b>Conf. No.</b>	8337
	<b>Submitted on:</b>	November 9, 2009

#### U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-cla	Filing Date
	1.	7,390,537	06.24.08	Wu et al.			
	2.	7,381,659 B2	06.2008	Nguyen et al.			
	3.	2008/0009141 A1	01.2008	Dubois et al.			
	4.	2008/0132055 A1	06.2008	Nguyen et al.			
	5.	7,341,761	03.11.08	Wu et al.			
	6.	7,381,662	06.03.08	Niu et al.			
	7.	6,5702,56	05.2003	Conti et al.			
	8.	2005/0260357	11.2005	Zheng et al.			
	9.	2008/0194105	08.2008	Dominquez et al.			
	10.	2003/0203652	12.2003	Bao et al.			
	11.	2004/0099952	5.2004	Goodner et al.			
	12.	2006/0027929	2.2006	Cooney et al.			
	13.	2006/0145304	7.2006	Boyanov et al.			
	14.	7,208,389	4.2007	Tipton et al.			
	15.	7,288,292	10.2007	Gates et al.			
	16.	6,410,462	06.2002	Yang et al.			
	17.	7,473,653	06.2007	Wu et al.			
	18.	6,890,850	5.2005	Lee et al.			
	19.	2004/0166240 A1	08.2004	Rhee et al.			
	20.	2005/0025892 A1	02.2005	Satoh et al.			
	21.	2006/0024976 A1	02.2006	Waldfried et al.			
	22.	6,436,824	08.2002	Chooi et al.			
	23.						

#### Foreign Patent or Published Foreign Patent Application

Examiner Initial		Document No.	Publication Date	Country or Patent Office	Class	Sub-Class	Translation	
							Yes	No

<b>Examiner</b>	<b>Date Considered</b>
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Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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	24.						
	25.						

**Other Documents**

<b>Examiner Initial</b>	<b>No.</b>	<b>Author, Title, Place (e.g. Journal) of Publication, Date</b>
	26.	U.S. Office Action mailed March 31, 2008, from U.S Application No. 10/820,525 [Att Dkt No. NOVLP091/NVLS-2889].
	27.	U.S. Office Action dated July 10, 2008, from U.S. Application No. 10/807,680 [Atty Dkt: NOVLP97/NVLS-2906]
	28.	U.S. Office Action mailed August 5, 2008, from U.S Application No. 10/987,208 [Att Dkt No. NOVLP104/NVLS-2928].
	29.	U.S. Final Office Action mailed May 29, 2008, from U.S Application No. 11/764,750 [Atty Dkt No. NOVLP106D1/NVLS-2930D1].
	30.	U.S. Notice of Allowance and Fee Due mailed August 25, 2008, from U.S. Application No. 11/764,750. [NOVLP106D1/NVLS-2930D1]
	31.	Allowed Claims from U.S. Application No. 11/764,750. [NOVLP106D1/NVLS-2930D1]
	32.	Solomons and Fryhle, Organic Chemistry, 9 <sup>th</sup> Edition, John Wiley & Sons, Inc., 2008, pages 602-603
	33.	Wu et al., Methods for Fabricating High Hardness/Modulus Low Dielectric Constant Materials," Novellus Systems, Inc., App. No. 11/369,658, filed March 6, 2006. [NOVLP148/NVLS-3111]
	34.	Szekeres, A et al., "Plasma-assisted chemical vapor depositing silicon oxynitride as an alternative material for gate dielectric in MOS devices." Microelectronics Journal 37 (2006) pp. 64-70.
	35.	U.S. Office Action for Application No. 11/369,658 mailed 12/12/2008 [Attorney Docket No. NOVLP148]
	36.	U.S. Office Action for Application No. 10/987,208 mailed 2/4/2009 [Attorney Docket No. NOVLP104]
	37.	U.S. Office Action for Application No. 11/606,340 mailed 2/5/2009 [Attorney Docket No. NOVLP100C1]
	38.	U.S. Office Action for Application No. 11/936,754 mailed 6/19/2009 [Attorney Docket No.: NOVLP098D1]
	39.	U.S. Final Office Action for Application No. 10/987,208 mailed 7/10/2009 [Attorney Docket No. NOVLP104]
	40.	U.S. Office Action for Application No. 11/369,658 mailed 7/8/09 [Attorney Docket No. NOVLP148]
	41.	Wu et al., PECVD Methods For Producing Ultra Low-K Dielectric Films Using UV Treatment," Novellus Systems, Inc., App. No. 11/608,056, filed December 7, 2006. [NOVLP196/NVLS-3238]

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	42.	U.S. Office Action for Application No. 11/608,056 mailed 8/20/09 [Attorney Docket No. NOVLP196/NVLS-3238]
	43.	Wu et al., Methods For Improving Performance of ODC Films With Dielectric Constant < 4.0,” Novellus Systems, Inc., App. No. 11/693,661, filed March 29, 2007. [NOVLP200/NVLS-3269]
	44.	U.S. Office Action for Application No. 11/693,661 mailed August 28, 2009 [Attorney Docket No. NOVLP200]
	45.	Wu et al., “Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups”, U.S. Application No. 12/348,791, filed January 5, 2009 [Atty Dkt: NOVLP106D1C1/NVLS-2930D2]
	46.	Wu et al., “Methods For Producing Low Stress Porous Low-K Dielectric Materials Using Precursors With Organic Functional Groups”, U.S. Application No. 12/479,114, filed June 5, 2009 [Atty Dkt: NOVLP106D1C2/ NVLS-2930D1C2]
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